In the Specification:

Please amend the Related Application section at page 1, lines 1-6 as follows:

Related Application

This application is a divisional of U.S. Application Serial No. 10/028,187, filed December 20, 2001, now United States Patent No. 6,653,186, which claims the benefit of priority from Korean Application No. 2000-82066, filed December 26, 2000, the disclosures of which are hereby incorporated herein by reference as if recited in their entirety.

Please replace the paragraph at page 7, lines 5-15, with the following amended paragraph:

As illustrated in **FIG. 8**, a first capacitor dielectric layer **112** is formed over the entire surface of the integrated circuit device. The first capacitor dielectric layer **112** is typically an amorphous layer that adheres well to the etch stop layer **108** and a subsequent U-shaped lower electrode, thus, the number of voids on the interface between the etch stop layer **108** and the first capacitor dielectric layer **112** may be reduced. The first capacitor dielectric layer **112** may include, for example, a dielectric material including tantalum oxide that may not be etched by an oxide etchant. The thickness of the first capacitor dielectric layer **112** is typically minimized to prevent an increase in capacitance. For example, if a second capacitor dielectric layer has a thickness of from about 100 to about 200 [[D]] Å, the thickness of the first capacitor dielectric layer **112** is typically from about 10 to about 40 [[D]] Å.

Please replace the paragraph at page 7, line 27 to page 8, line 2, with the following amended paragraph:

A conductive layer **114**, *i.e.* a U-shaped lower electrode, is formed on the surface of the integrated circuit device as illustrated in **FIG. 9**. The conductive layer **114** is formed on the inner surface of the first capacitor dielectric layer **112**, on the surface of the plug **104**, and

on the surface of the upper mold layer pattern **110**. The conductive layer **114** may be formed using, for example, precious metal layers of a platinum group, such as a platinum (Pt) layer, a ruthenium (Ru) layer and an iridium (Ir) layer. The conductive layer **114** for the U-shaped lower electrode may have a thickness of from about 200 to about 500 [[D]] Å. The conductive layer **114** for the U-shaped lower electrode may be formed using a chemical vapor deposition (CVD) method having excellent step coverage.